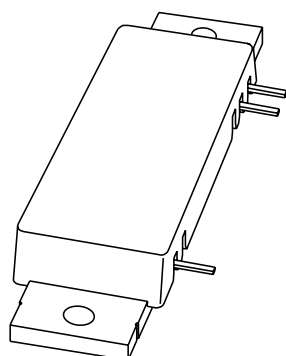


DATA SHEET



BGF1901-10 GSM1900 EDGE power module

Product specification
Supersedes data of 2003 Nov 17

2004 Oct 11

GSM1900 EDGE power module**BGF1901-10****FEATURES**

- Typical GSM EDGE performance at a supply voltage of 26 V:
 - Output power = 3.5 W
 - Gain = 26.5 dB
 - Efficiency = 19 %
 - ACPR < –63 dBc at 400 kHz
 - rms EVM < 1.2 %
 - peak EVM < 3.6 %.
- Low distortion to a CDMA signal
- Excellent 2-tone performance
- Low die temperature due to copper flange
- Integrated temperature compensated bias
- 50 Ω input/output system
- Flat gain over frequency band.

APPLICATIONS

- Base station RF power amplifiers in the 1930 to 1990 MHz frequency range
- GSM, GSM EDGE, multi carrier applications
- Macrocell (driver stage) and Microcell (final stage).

DESCRIPTION

10 W LDMOS power amplifier module for base station amplifier applications in the 1930 to 1990 MHz band.

QUICK REFERENCE DATA

Typical RF performance at $T_{mb} = 25\text{ }^{\circ}\text{C}$; $Z_S = Z_L = 50\text{ }\Omega$.

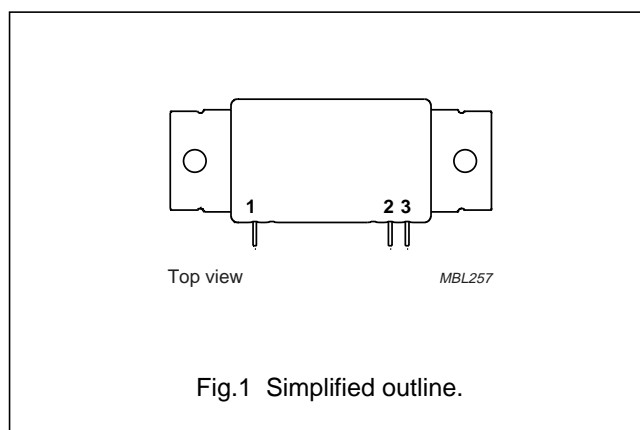
MODE OF OPERATION	f (MHz)	V _S (V)	P _L (W)	G _p (dB)	η (%)	ACPR (dBc)	rms EVM (%)
CW	1930 to 1990	26	10	25.5	34	–	–
GSM EDGE	1930 to 1990	26	3.5	26.5	19	–63 ⁽¹⁾	1.2

Note

1. ACPR 400 kHz at 30 kHz resolution bandwidth.

PINNING - SOT365C

PIN	DESCRIPTION
1	RF input
2	V _S
3	RF output
Flange	ground



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ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BGF1901-10	–	plastic rectangular single-ended flat package; flange mounted; 2 mounting holes; 3 in-line leads	SOT365C

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
V_S	DC supply voltage	–	30	V
P_D	input drive power	–	100	mW
P_L	load power	–	15	W
T_{stg}	storage temperature	–30	+100	°C
T_{mb}	operating mounting base temperature	–20	+85	°C

CHARACTERISTICS

$T_{mb} = 25\text{ °C}$; $V_S = 26\text{ V}$; $P_L = 6\text{ W}$; $f = 1930\text{ to }1990\text{ MHz}$; $Z_S = Z_L = 50\text{ }\Omega$; unless otherwise specified.

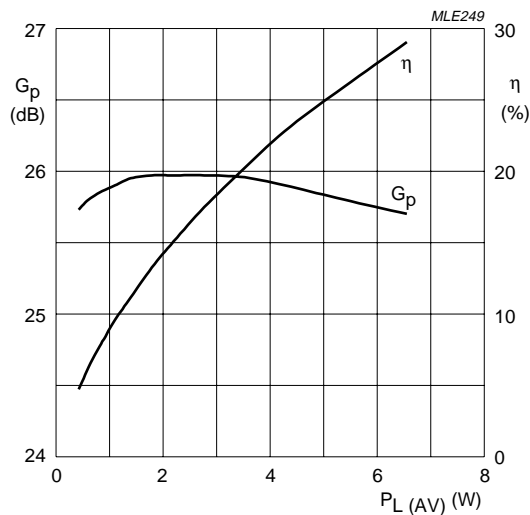
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
CW mode						
I_{DQ}	quiescent current (pin 2)	$P_D = 0\text{ mW}$	220	255	280	mA
P_{1dB}	load power	at 1 dB gain compression	7	10	–	W
G_p	power gain		24	26.5	30	dB
$\Delta G_{p(freq)}$	gain flatness over frequency range		–	0.7	2	dB
$\Delta G_{p(pwr)}$	gain flatness over power band	$P_L = 50\text{ mW}$ up to 5 W	–1	0	+1	dB
G_{OB}	out of band gain	small signal, $P_D = 0\text{ dBm}$; 1930 MHz > f > 1990 MHz	–	–	$G_{Pi\text{ max}} + 2$; note 1	dB
η	efficiency		22	25	–	%
$VSWR_{in}$	input VSWR		–	1.4 : 1	2 : 1	
H_2	second harmonic		–	–58	–50	dBc
H_3	third harmonic		–	–59	–53	dBc
GSM EDGE mode ($P_L = 3.5\text{ W}$ average)						
SR200	spectral regrowth; EDGE GSM signal	200 kHz; note 2	–	–37	–32	dBc
SR400		400 kHz	–	–63	–60	dBc
EVM_{rms}	rms EDGE signal distortion		–	1.2	2.5	%
EVM_M	peak EDGE signal distortion		–	3.6	8	%

Notes

- G_{Pi} is small signal in-band gain.
- As defined by ETSI.

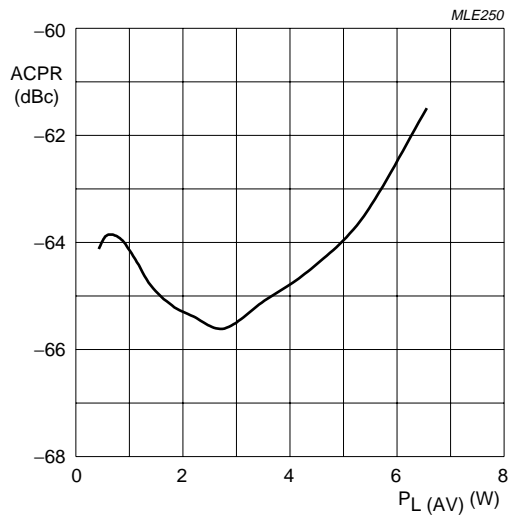
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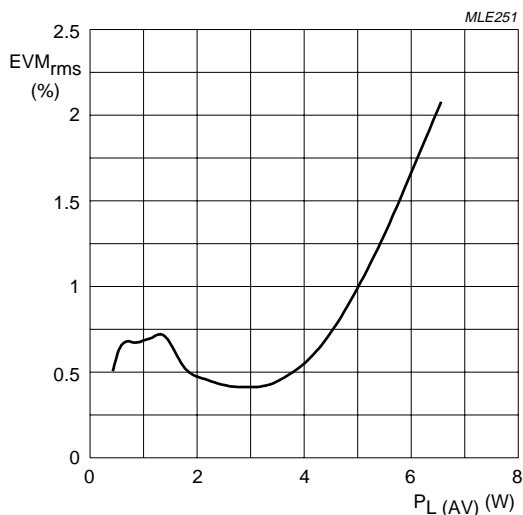
f = 1960 MHz.

Fig.2 GSM EDGE power gain and efficiency as functions of load power; typical values.



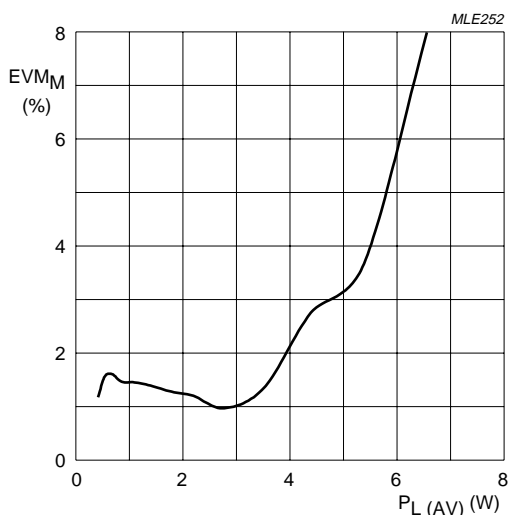
f = 1960 MHz.

Fig.3 GSM EDGE ACPR at 400 kHz as a function of load power; typical values.



f = 1960 MHz.

Fig.4 GSM EDGE rms EVM as a function of average load power; typical values.

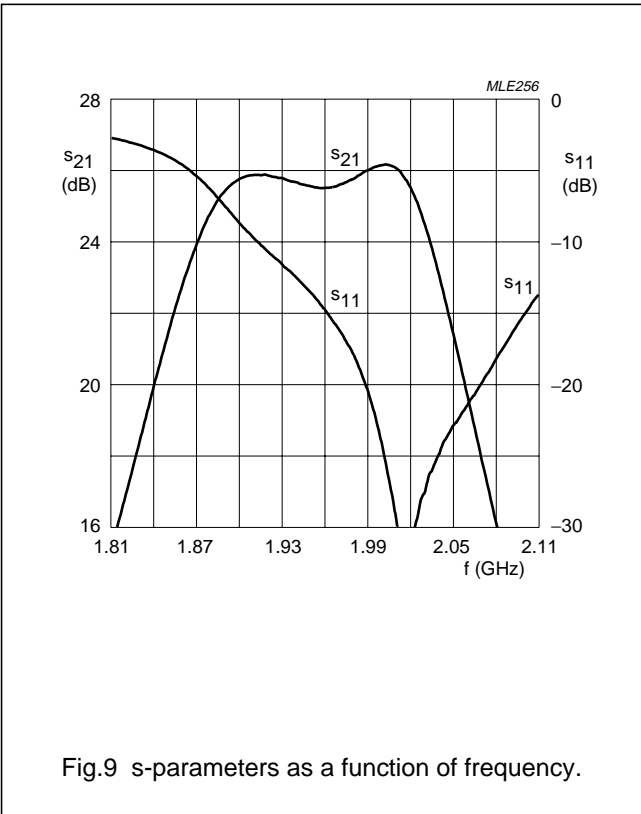
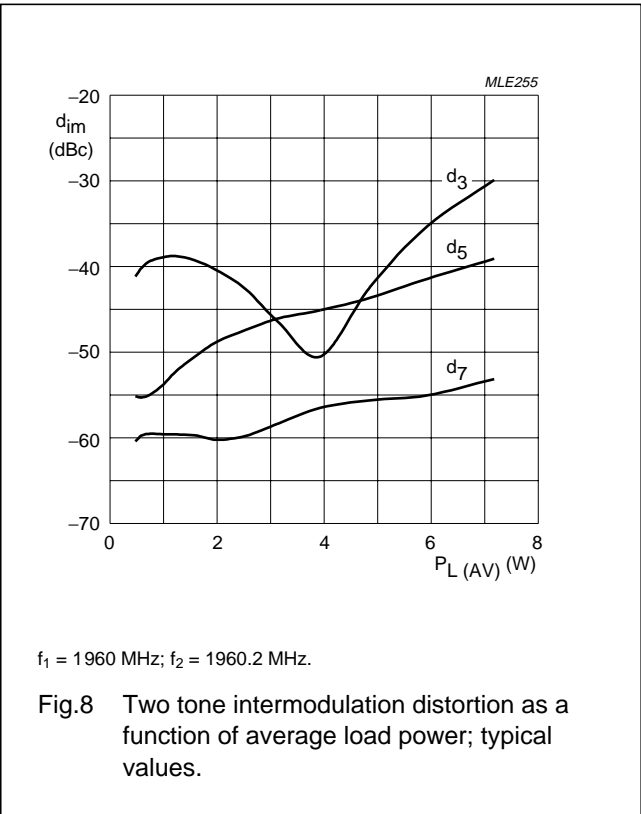
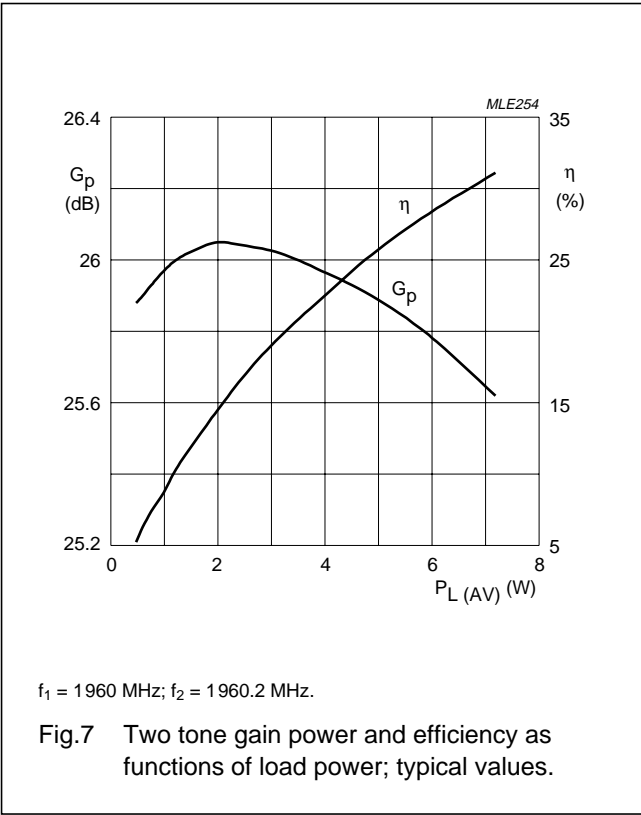
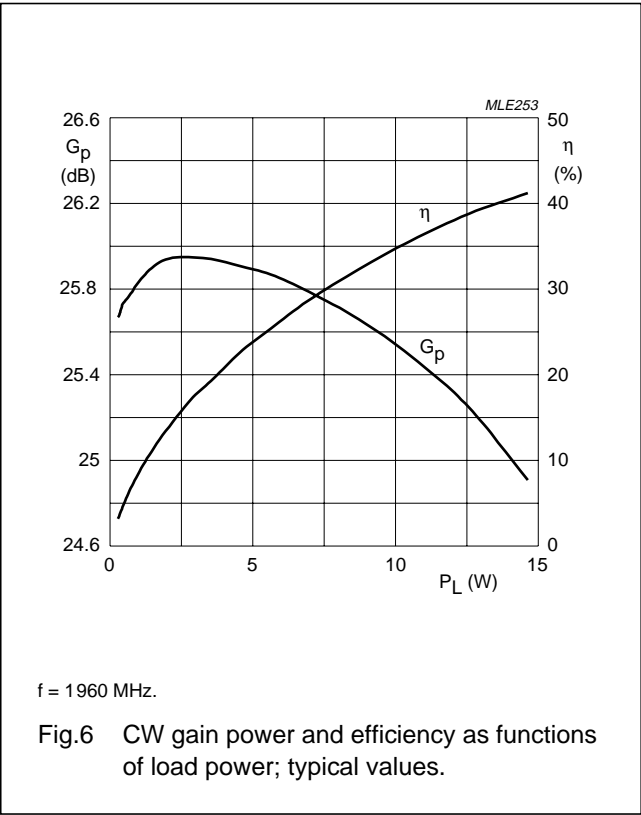


f = 1960 MHz.

Fig.5 GSM EDGE peak EVM as function of average load power; typical values.

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MOUNTING RECOMMENDATIONS**General**

LDMOS Tbase station modules are manufactured with the dies directly mounted onto a copper flange. The matching and bias circuit components are mounted on a printed-circuit board (PCB), which is also soldered onto the copper flange. The dies and the PCB are encapsulated in a plastic cap, and pins extending from the module provide a means of electrical connection. This construction allows the module to withstand a limited amount of flexing, although bending of the module is to be avoided as much as possible. Mechanical stress can occur if the bottom surface of the module and the surface of the amplifier casing (external heatsink) are not mutually flat. This, therefore, should be a consideration when mounting the module in the amplifier. Another cause of mechanical stress can arise from thermal mismatch after soldering of the pins. Precautions should be taken during soldering, and efforts made to ensure a good thermal contact between the flange and the external heatsink.

External heatsink (amplifier casing)

The module should always be mounted on a heatsink with a low thermal resistance to keep the module temperature as low as possible. The mounting area of the heatsink should be flat and free from burrs and loose particles. We recommend a flatness for the mounting area of between 50 µm concave and 50 µm convex. The 50 µm concave value is to ensure optimal thermal behaviour, while the 50 µm convex value is intended to limit mechanical stress due to bending.

In order to ensure optimum thermal behaviour, the use of thermal compound is recommended when mounting the module onto the amplifier external heatsink.

The following recommended thermal compounds have a thermal conductivity of >0.5 W/mK:

- WPS II (silicone-free) from Austerlitz-Electronics
- Comp. Trans. from KF
- 340 from Dow Corning
- Trans-Heat from E. Friis-Mikkelsen.

The use of thermal pads instead of thermal compound is not recommended as the pads may not maintain a uniform flatness over a period of time.

Mounting**PREPARATION**

Ensure that the surface finishes are free from burrs, dirt and grease.

CAUTION

During the following procedures ESD precautions should be taken to protect the device from electrostatic damage.

PROCEDURE

1. Apply a thin, evenly spread layer of thermal compound to the module flange bottom surface. Excessive use of thermal compound may result in increased thermal resistance and possible bending of the of the flange. Too little thermal compound will result in an increase in thermal resistance.
2. Take care that there is some space between the cap and the PCB. Bring the module into contact with the external heatsink casing, ensuring that there is sufficient space for any excess thermal compound to escape.
3. Carefully align the module with the heatsink casing mounting holes, and secure with two 3 mm bolts and two flat washers. Initially tighten the bolts to "finger tight" (approximately 0.05 Nm). Using a torque wrench, tighten each bolt in alternating steps to a final torque of 0.4 Nm.
4. After the module is secured to the casing, the module leads may be soldered to the PCB. The leads are for electrical connection only, and should not be used to support the module at any time in the assembly process.

A soldering iron may be used up to a temperature of 250 °C for a maximum of 10 seconds. Avoid contact between the soldering iron and the plastic cap.

Electrical connections

The main ground path of all modules is via the flange. It is therefore important that the flange is well grounded and that return paths are kept as short as possible. An incorrectly grounded flange can result in a loss of output power or oscillation.

The RF input and output of the module are designed for 50 Ω connections.

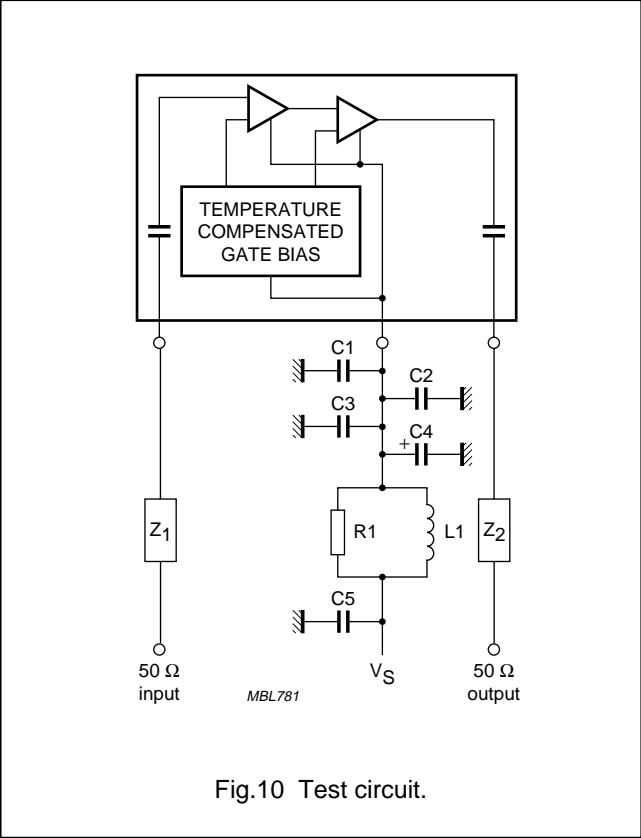
Incoming inspection

When incoming inspection is performed, use a properly designed test fixture to avoid excessive mechanical stress and to ensure optimal RF performance. Philips can deliver dedicated test fixtures on request.

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APPLICATION INFORMATION



List of components (see Figs 10 and 11)

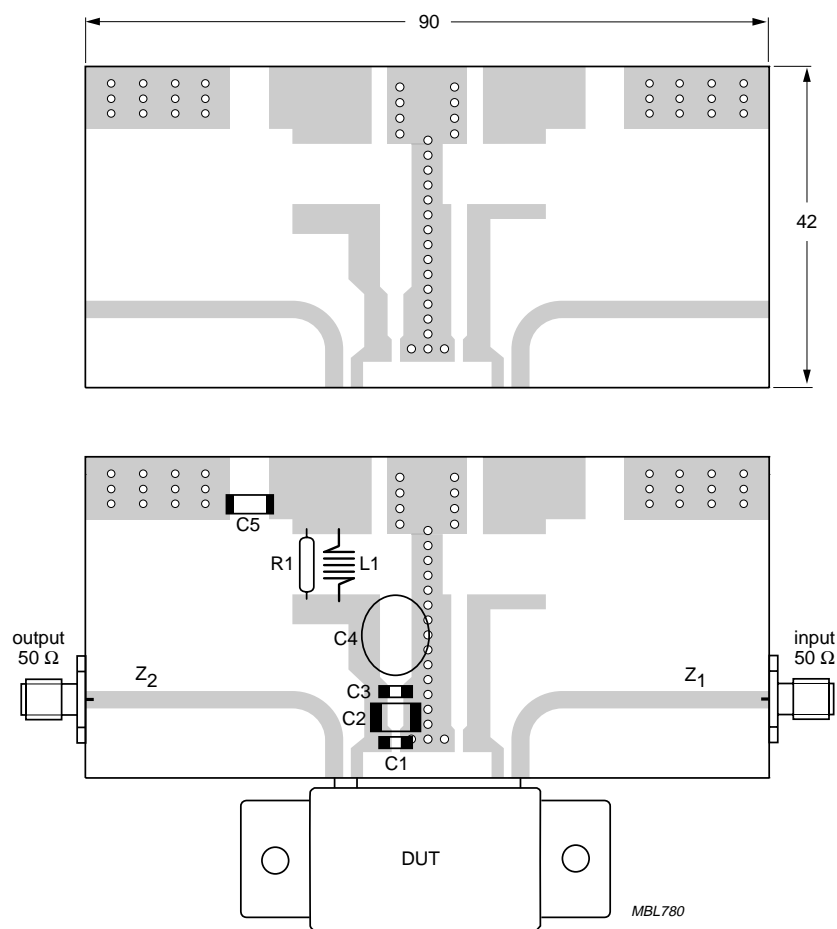
COMPONENT	DESCRIPTION	VALUE	CATALOGUE NUMBER
C1, C3	multilayer X7R ceramic chip capacitor	100 nF; 50 V	
C2, C5	tantalum SMD capacitor	10 µF; 35 V	
C4	electrolytic capacitor	100 µF; 35 V	
L1	grade 4S2 Ferroxcube bead		4330 030 36300
R1	metal film resistor	10 Ω; 0.4 W	2322 195 13109
Z1, Z2	stripline; note 1	50 Ω	

Note

1. The striplines are on a double copper-clad printed-circuit board (RO5880) with $\epsilon_r = 2.2$ and thickness = 0.79 mm.

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Dimensions in mm.

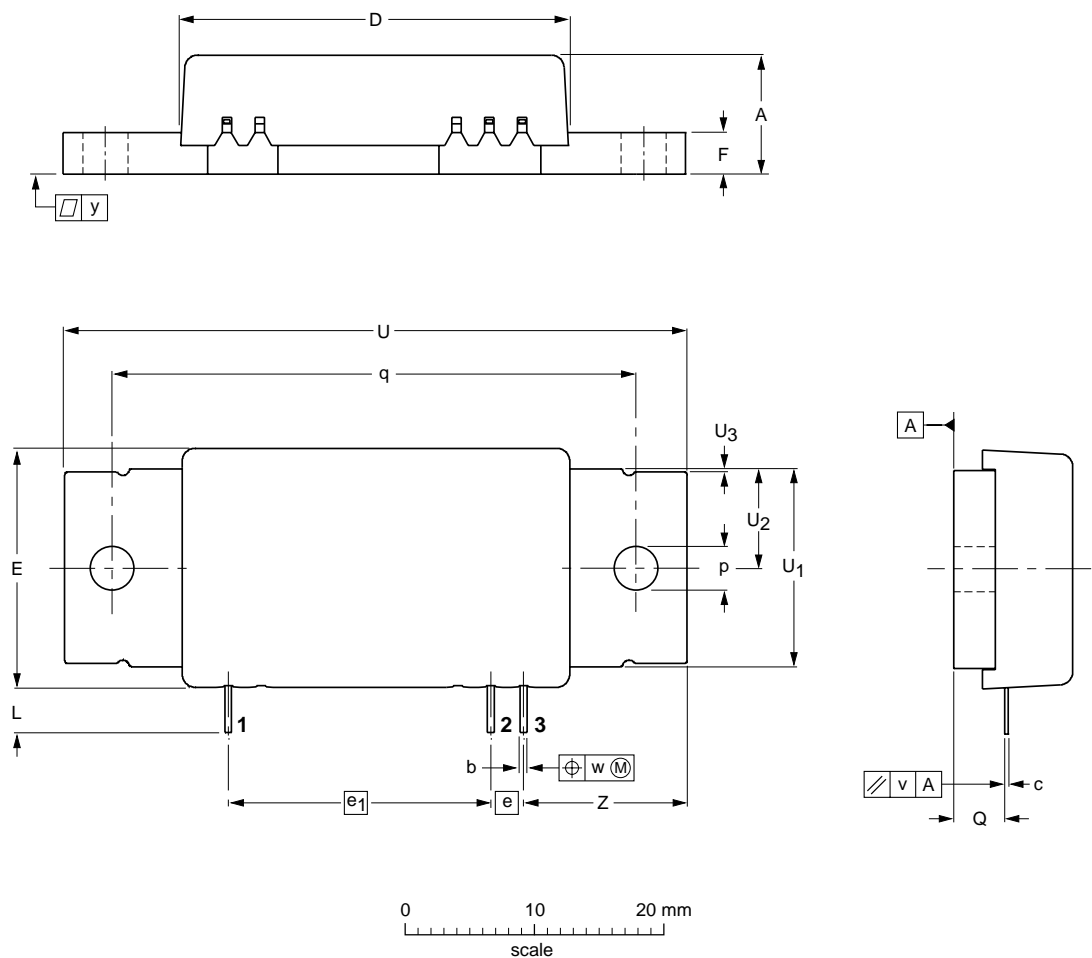
Fig.11 Printed-circuit board and component layout.

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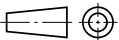
PACKAGE OUTLINE

Plastic rectangular single-ended flat package; flange mounted; 2 mounting holes; 3 in-line leads SOT365C



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	c	D	E	e	e ₁	F	L	p	Q	q	U	U ₁	U ₂	U ₃	v	w	y	Z
mm	9.5 9.0	0.56 0.46	0.3 0.2	30.1 29.9	18.6 18.4	2.54	20.32	3.3 3.1	3.7 3.3	3.55 3.45	4.0 3.8	41.75 41.65	48.4 48.0	15.4 15.2	7.75 7.55	1.1 0.0	0.3	0.25	0.1	12.8 12.6

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT365C						01-06-06 02-11-13

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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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